



**SEMITRANS™ M1**

## Power MOSFET Modules

### SKM 111AR

#### Features

- N Channel, enhancement mode
- Avalanche characteristic
- Short connections and built-in gate resistors to suppress internal oscillations even in critical applications
- Isolated copper baseplate
- All electrical connections on top for easy busbaring
- Large clearances (10 mm) and creepage distances (20 mm)
- UL recognized, file no. E 63 532

#### Typical Applications\*

- Switched mode power supplies
- DC servo and robot drives
- DC choppers
- UPS equipment
- Not suitable for linear amplification



**MA**

| Absolute Maximum Ratings |                           | $T_c = 25\text{ °C}$ , unless otherwise specified |       |
|--------------------------|---------------------------|---|-------|
| Symbol                   | Conditions                | Values  | Units |
| $V_{DS}$                 |                           | 100   | V     |
| $I_D$                    | $T_s = 25\text{ (80) °C}$ | 200 (150)   | A     |
| $I_{DM}$                 | 1 ms                      | 600   | A     |
| $V_{GS}$                 |                           | $\pm 20$  | V     |
| $T_{vj}$ ( $T_{stg}$ )   |                           | - 40 ... + 150 (125)                              | °C    |
| $V_{isol}$               | AC, 1 min.                | 2500  | V     |
| Inverse diode            |                           |   |       |
| $I_F = -I_S$             |                           | 200   | A     |
| $I_{FM} = -I_{SM}$       |                           | 600   | A     |

| Characteristics         |   | $T_c = 25\text{ °C}$ , unless otherwise specified |          |            |               |
|-------------------------|---|---|----------|------------|---------------|
| Symbol                  | Conditions  | min.  | typ.     | max.       | Units         |
| $V_{(BR)DSS}$           | $V_{GS} = 0\text{ V}$ , $I_D = 0,25\text{ mA}$                                  | 100   |          |            | V             |
| $V_{GS(th)}$            | $V_{GS} = V_{DS}$ , $I_D = 1\text{ mA}$   | 2,1   | 3        | 4          | V             |
| $I_{DSS}$               | $V_{GS} = 0\text{ V}$ , $V_{DS} = 100\text{ V}$ ,<br>$T_j = 25\text{ (125) °C}$ |   | 50 (300) | 250 (1000) | $\mu\text{A}$ |
| $I_{GSS}$               | $V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$                                  |   | 10       | 100        | nA            |
| $R_{DS(on)}$            | $V_{GS} = 10\text{ V}$ , $I_D = 130\text{ A}$                                   |   | 7        | 8,5        | m $\Omega$    |
| $g_{fs}$                | $V_{DS} = 25\text{ V}$ , $I_D = 130\text{ A}$                                   | 60  | 75       |            | S             |
| $C_{CHC}$               | $V_{GS} = 0$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$                      |   |          | 160        | pF            |
| $C_{iss}$               |   |   | 10       | 13         | nF            |
| $C_{oss}$               |   |   | 5        | 7,5        | nF            |
| $C_{rss}$               |   |   | 1,8      | 2,7        | nF            |
| $L_{DS}$                |   |   |          | 20         | nH            |
| $t_{d(on)}$             | $V_{DD} = 50\text{ V}$ , $I_D = 130\text{ A}$ ,                                 |   | 60       |            | ns            |
| $t_r$                   | $V_{GS} = 10\text{ V}$ , $R_G = 3,3\ \Omega$                                    |   | 220      |            | ns            |
| $t_{d(off)}$            |   |   | 270      |            | ns            |
| $t_f$                   |   |   | 200      |            | ns            |
| Inverse diode           |   |   |          |            |               |
| $V_{SD}$                | $I_F = 400\text{ A}$ ; $V_{GS} = 0\text{ V}$                                    |   | 1,25     | 1,6        | V             |
| $t_{rr}$                | $T_j = 25\text{ (150) °C}$  |   | 400      |            | ns            |
| $Q_{rr}$                | $T_j = 25\text{ °C}$  |   | 3,5      |            | $\mu\text{C}$ |
| $I_{rr}$                | $T_j = 150\text{ °C}$   |   |          |            | A             |
| Thermal characteristics |   |   |          |            |               |
| $R_{th(j-c)}$           | per MOSFET  |   |          | 0,18       | K/W           |
| $R_{th(c-s)}$           | $M_s$ , surface 10 $\mu\text{m}$ , per module                                   |   |          | 0,05       | K/W           |
| Mechanical data         |   |   |          |            |               |
| $M_s$                   | to heatsink (M6)  | 4   |          | 5          | Nm            |
| $M_t$                   | for terminals (M5)  | 2,5   |          | 3,5        | Nm            |
| w                       |   |   |          | 130        | g             |

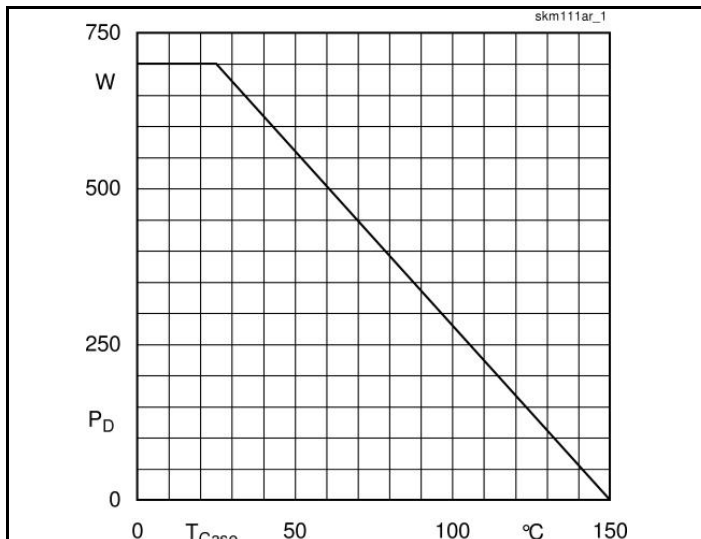


Fig. 1 Rated power dissipation vs. temperature

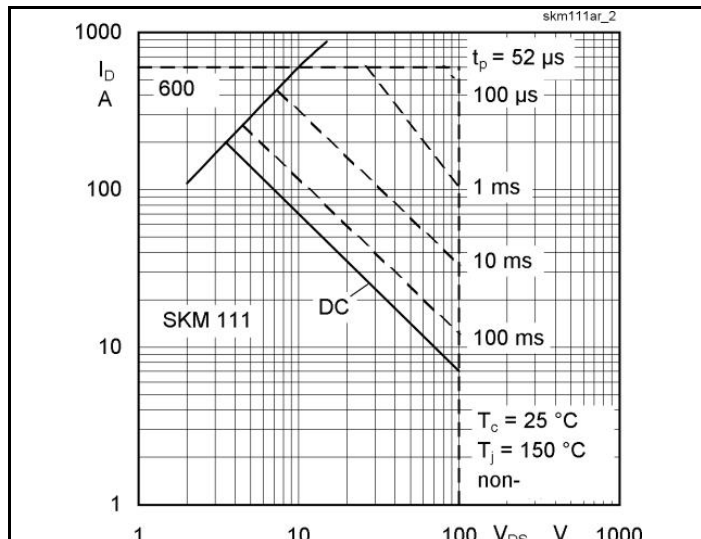


Fig. 2 Maximum safe operating area

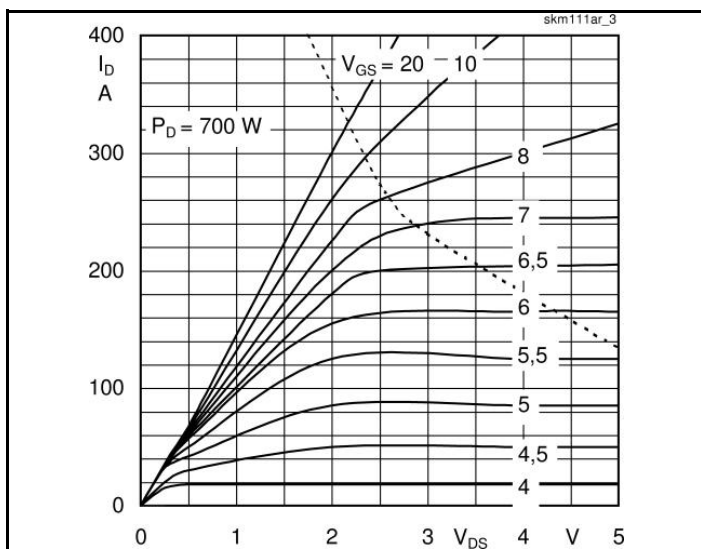


Fig. 3 Output characteristic

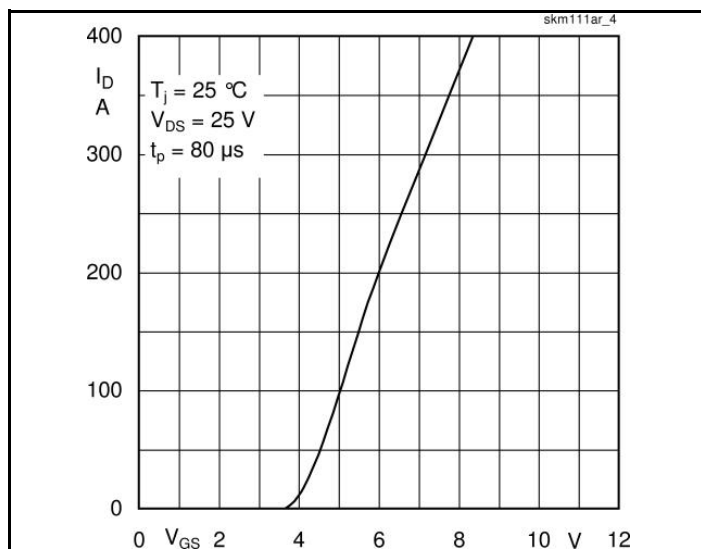


Fig. 4 Transfer characteristic

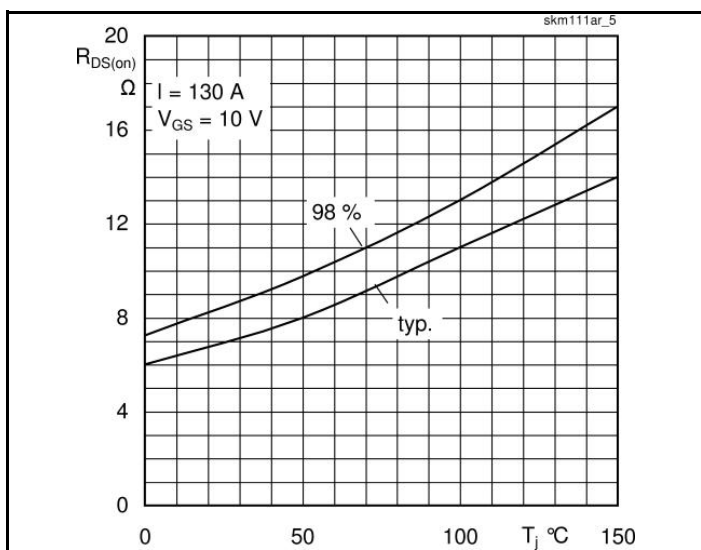


Fig. 5 On-resistance vs. temperature

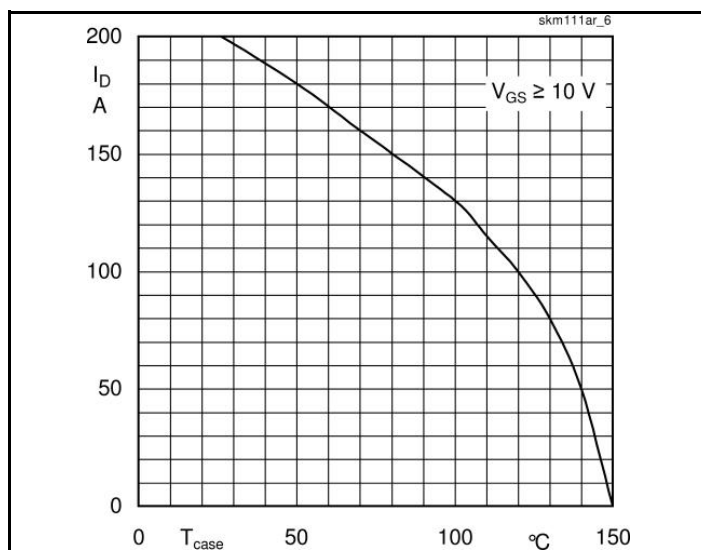


Fig. 6 Rated current vs. temperature

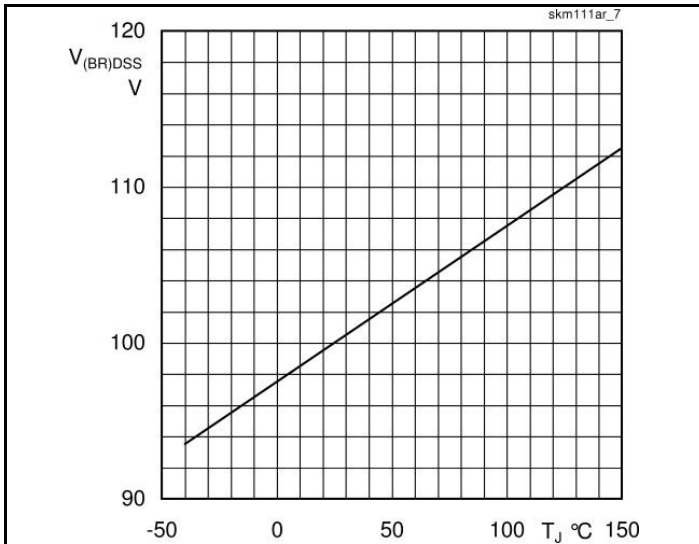


Fig. 7 Brakdown voltage vs. temperature

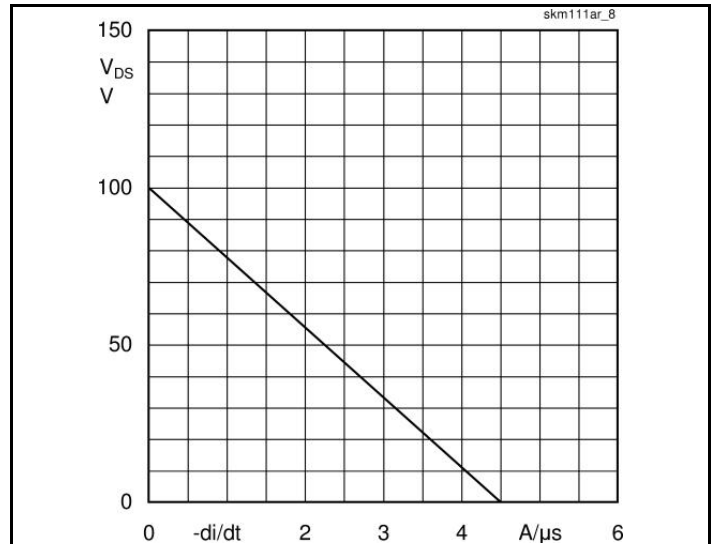


Fig. 8 Drain-source voltage derating

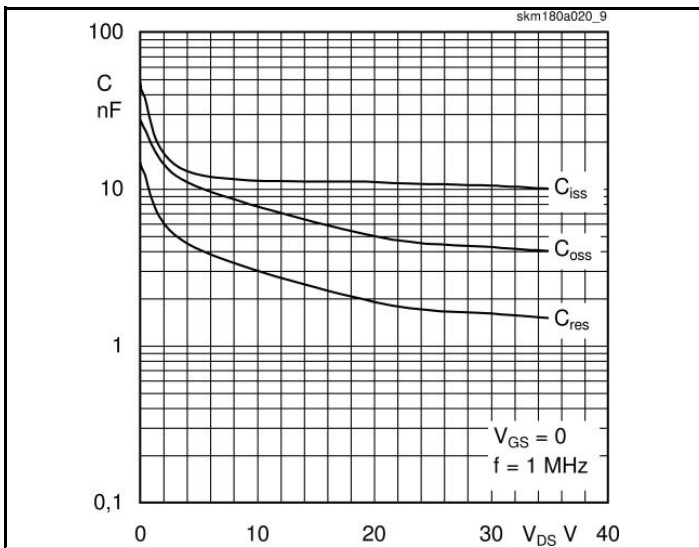


Fig. 9 Capacitances vs. drain-source voltage

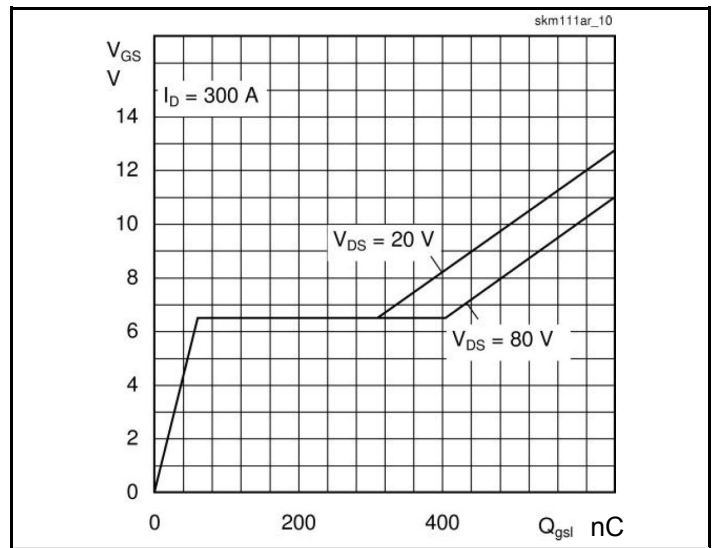


Fig. 10 Gate charge characteristic

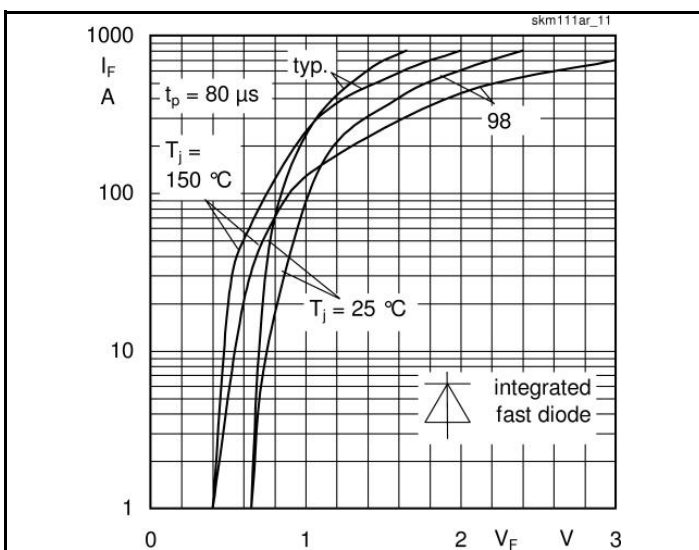


Fig. 11 Diode forward characteristic

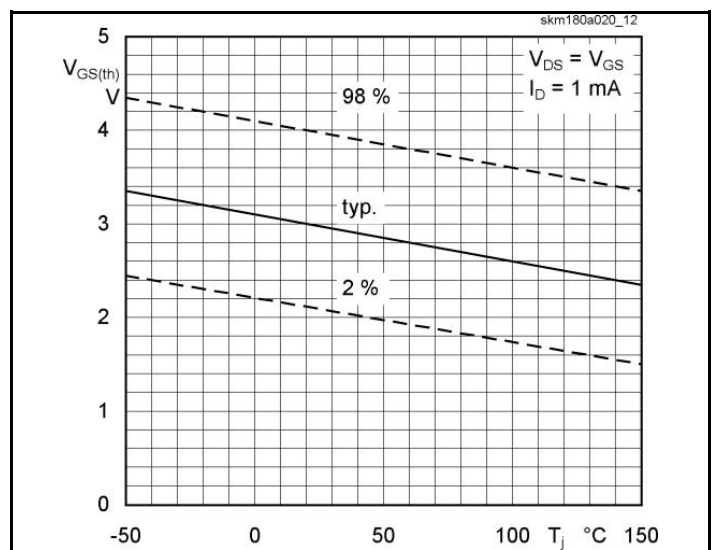
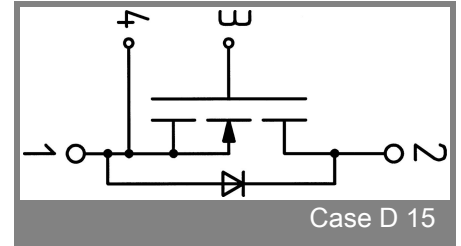
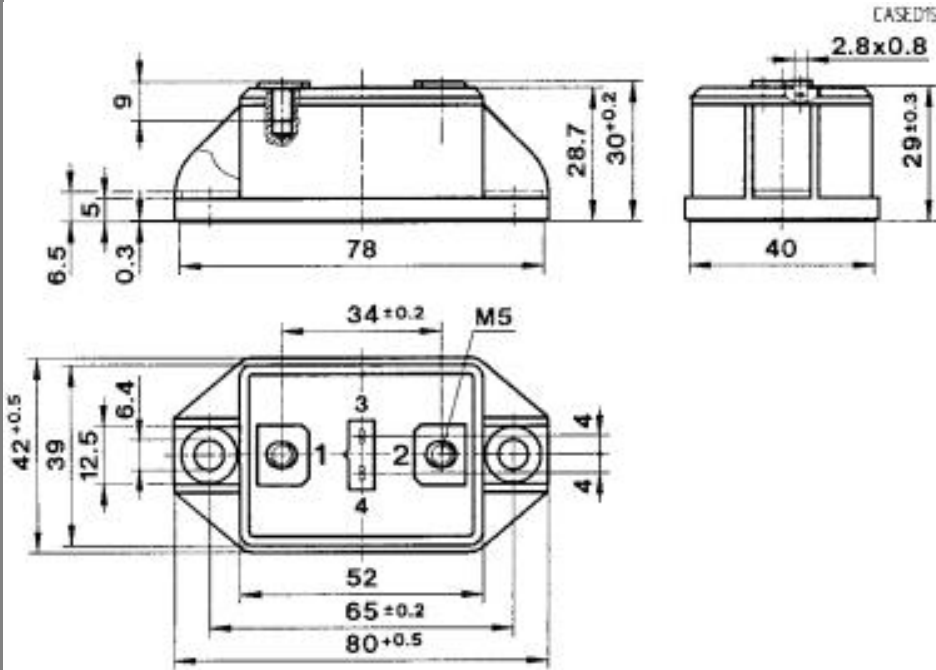


Fig. 14 Gate-source threshold voltage

UL Recognized  
File no. E 63 532

Dimensions in mm



Case D 15

Case D15

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

#### \*IMPORTANT INFORMATION AND WARNINGS

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